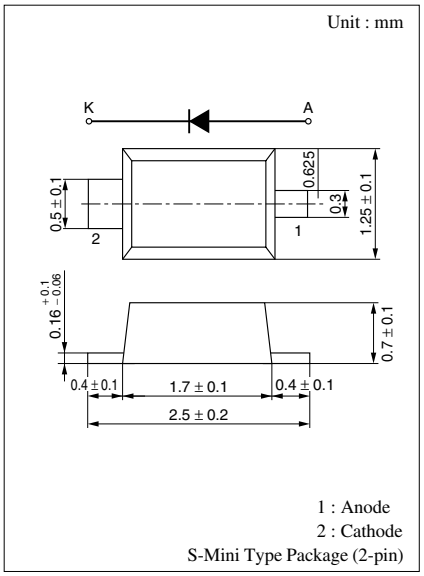
MA2ZD02

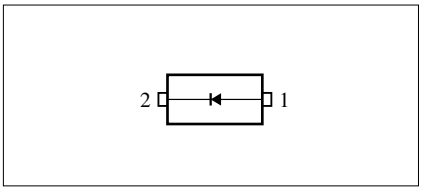
Silicon epitaxial planar type

For high-frequency rectification



Marking Symbol: 2H

Internal Connection



■ Features

- Mini package (S-mini type 2-pin)
- Reverse current (DC value) V_R is low

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	20	V
Average forward current	$I_{F(AV)}$	500	mA
Non-repetitive peak forward surge current*	I_{FSM}	3	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

Note) *: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

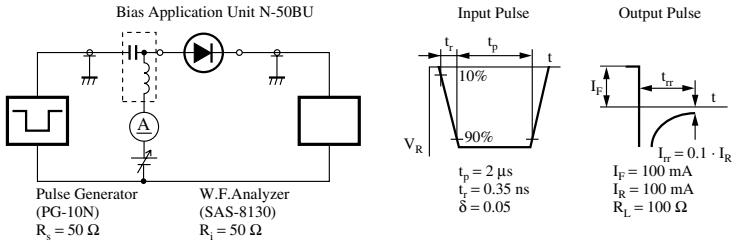
■ Electrical Characteristics $T_a = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_{R1}	V_R = 5 V			1	μA
	I_{R2}	V_R = 10 V			10	μA
Forward voltage (DC)	V_{F1}	I_F = 10 mA		0.3	0.4	V
	V_{F2}	I_F = 500 mA		0.5	0.55	V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz		60		pF
Reverse recovery time*	t_{rr}	$I_F = I_R$ = 100 mA $I_{rr} = 0.1 \cdot I_R$, R_L = 100 Ω		5		ns

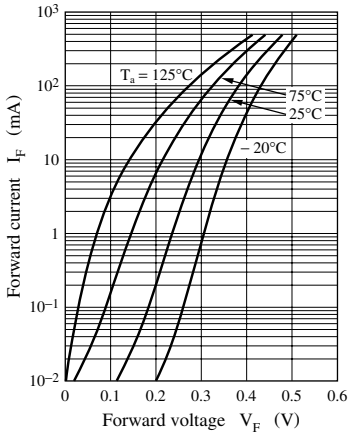
Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment

2. Rated input/output frequency: 1 000 MHz

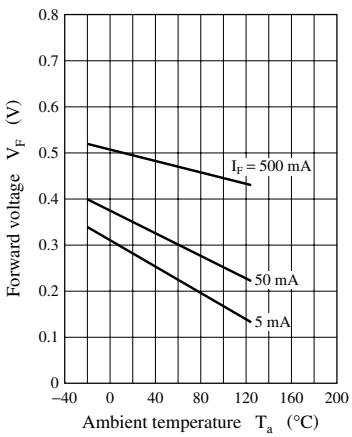
3. *: t_{rr} measuring instrument



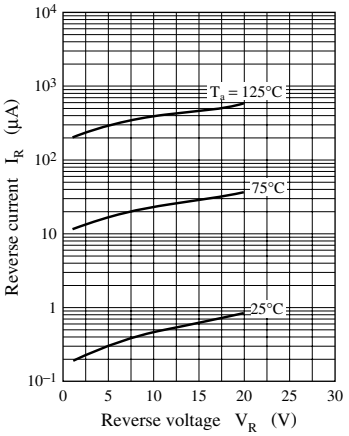
I_F — V_F



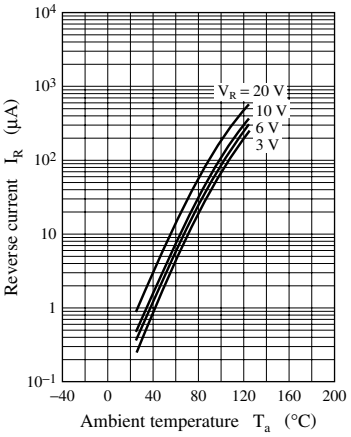
V_F — T_a



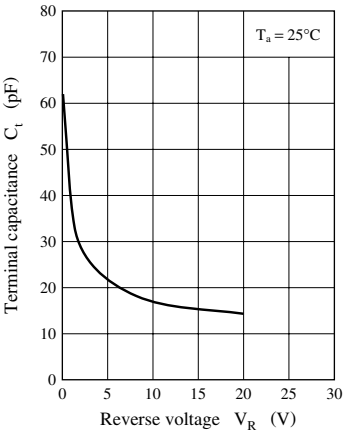
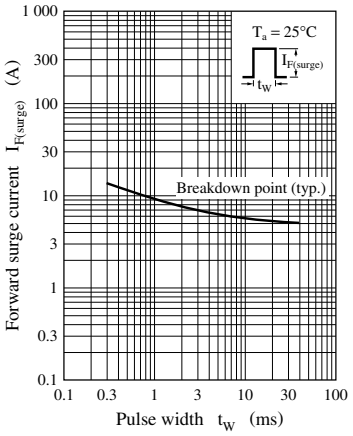
I_R — V_R



I_R — T_a



C_t — V_R



$I_{F(surge)}$ — t_W